

30V P-Channel Enhancement Mode MOSFET

Voltage -30 V Current -5 A

Features

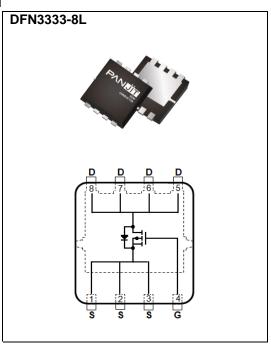
- $R_{DS(ON)}$, V_{GS} @-10V, I_D @-3A<50m Ω
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_D@-2A<80m\Omega$
- High switching speed
- Improved dv/dt capability
- Low gate charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.03 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	-30	V	
Gate-Source Voltage		V _{GS}	<u>+</u> 20		
Continuous Drain Current	T _A =25°C	l _D	-5.0	А	
	T _A =70°C		-4.0		
Pulsed Drain Current ^(Note 1)		I _{DM}	-20		
Power Dissipation	T _A =25°C		2.0	W	
Power Dissipation	T _A =70°C	PD	1.3		
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C	
Typical Thermal Resistance Junction to Ambient ^(Note 5)		R _{θJA}	62.5	°C/W	

Limited only By Maximum Junction Temperature



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-30	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} , I _D =-250uA	-1	-1.6	-2.5			
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-3A	-	40	50	mΩ		
		V _{GS} =-4.5V, I _D =-2A	-	60	80			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V	-	-	-1	uA		
Gate-Source Leakage Current	Igss	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA		
Dynamic ^(Note 6)								
Total Gate Charge	Q_g	\/ 45\/ L 0A	-	4.8	-	nC		
Gate-Source Charge	Q_{gs}	V _{DS} =-15V, I _D =-3A, V _{GS} =-4.5V ^(Note 1,2)	-	1.7	-			
Gate-Drain Charge	Q_{gd}	VGS=-4.5 V(1000 1)2/	-	1.7	-			
Input Capacitance	Ciss	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	-	516	-	pF		
Output Capacitance	Coss	V _{DS} =-15V, V _{GS} =0V,	-	83	-			
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	61	-			
Turn-On Delay Time	td _(on)	\/ 45\/ 1 40	-	5.6	-			
Turn-On Rise Time	V_{DS} =-15V, I_{D} =-1A,		-	8.5	-			
Turn-Off Delay Time	td _(off)	V _{GEN} =-10V, R _G =6 Ω	-	27	-	ns		
Turn-Off Fall Time	t _f	(1000 1,2)	-	18	-			
Drain-Source Diode								
Maximum Continuous Drain-Source	,				E	_		
Diode Forward Current	le Forward Current		-	-	-5	А		
Diode Forward Voltage	V _{SD}	I _S =-1A, V _{GS} =0V	-	-0.76	-1	V		

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

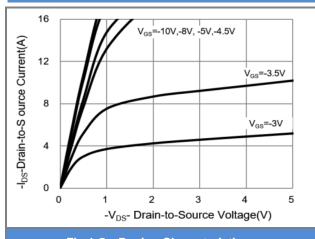


Fig.1 On-Region Characteristics

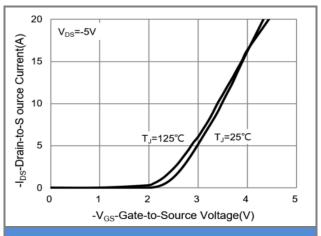


Fig.2 Transfer Characteristics

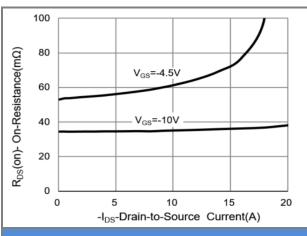


Fig.3 On-Resistance vs. Drain Current

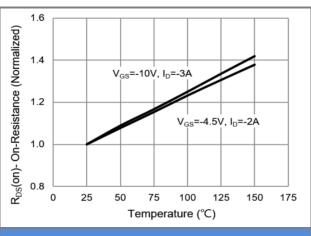


Fig.4 On-Resistance vs. Junction temperature

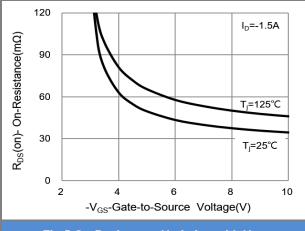


Fig.5 On-Resistance Variation with V_{GS}

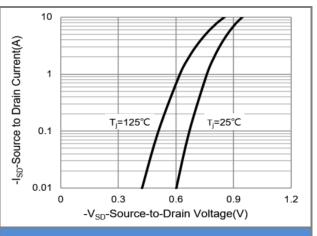


Fig.6 Source-Drain Diode Forward Voltage



TYPICAL CHARACTERISTIC CURVES

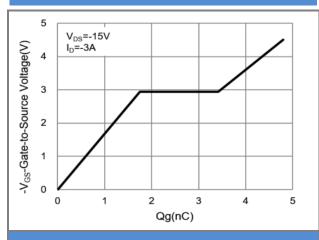


Fig.7 Gate-Charge Characteristics

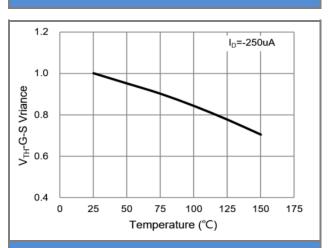


Fig.9 Threshold Voltage Variation with Temperature

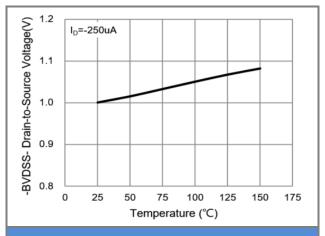


Fig.8 Breakdown Voltage Variation vs. Temperature

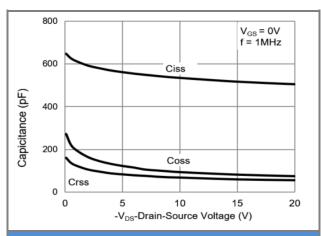


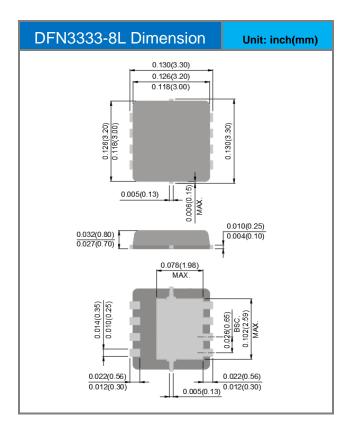
Fig.10 Capacitance vs. Drain-Source Voltage

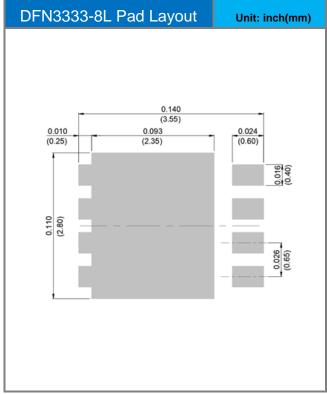


Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ4413P_R2_00001	DFN3333-8L	5K pcs / 13" reel	4413	Halogen free RoHS compliant

Packaging Information & Mounting Pad Layout







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